Insulator-M etal P hase D iagram of the Optim ally D oped M anganites from the D isordered H olstein-D ouble Exchange M odel

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W e study the H olstein-D ouble Exchange m odel in three dimensions in the presence of substitutional disorder. U sing a new M onte C arb technique we establish the phase diagram of the clean m odel and then focus on the e ect of varying electron-phonon coupling and disorder at xed electron density. W e demonstrate how extrinsic disorder controls the interplay of lattice polaron e ects and spin uctuations and leads to widely varying regimes in transport. Our results on the disorder dependence of the ferrom agnetic T_c and m etal-insulator transitions bear direct com parison to data on the optim ally doped', x = 0.3 0.4, m anganites. W e highlight disorder induced polaron form ation as a key e ect in these materials, organise a wide variety of data into a sim ple global phase diagram ', and m ake several experimental predictions.

The Holstein-Double Exchange (H-DE) model provides a minimal description of strongly coupled charge, spin, and lattice degrees of freedom, typical of the perovskite manganites $A_{1 x} A_x^0 M nO_3$ [1], and captures the interplay of polaronic tendency and spin disorder that occurs in these materials. A lithough a detailed solution has not been available in three dimensions (3D), the H-DE model is believed to describe the trend towards stronger localisation and weakened ferrom agnetism observed with reducing A site ionic radius (r_A) in the manganites.

The role of quenched disorder in these systems, arising, for example, from the cation size m ism atch ($_{\rm A}$) is only partially understood. Most of the disorder related theory [2,3] has focused on e ects near a rst order phase boundary, i.e., the bicritical' region [4], motivated by the observation of cluster coexistence in som e m aterials [5]. P hase competetion and bicriticality, how ever, occurs only in a limited part of the phase diagram. Studies with controlled variation in $_{\rm A}$ indicate that quenched disorder has a dram atic e ect on the ferrom agnetic T_c and resistivity [6[9], and optical response [10] even far from bicriticality. The origin of these e ects remain unexplained.

O ur prim ary contribution in this paper is to demonstrate how this unusual sensitivity arises due to a positive feedback of quenched disorder on the polaron form ation tendency, and its interplay with spin uctuations. Through a detailed real space solution of the disordered H \rightarrow E m odel on large 3D lattices we (i) demonstrate disorder controlled m etal-insulator transitions (M II), in the ground state and at nite tem perature, that are absent in the blean' system, (ii) explain the rapid suppression of T_c with increasing disorder, (iii) com pare our results in detail with data on the m anganites at x = 0.3 0.4, constructing a global phase diagram', and (iv) m ake testable predictions about the A dependence of optical spectral weight, lattice distortion, and tunneling density of states in the optim ally doped m anganites.

W e study the adiabatic disordered (d) H -D E m odel:

$$H = t (c_{i}^{y}c_{j} + hc) + (i) n_{i}$$

$$\lim_{hiji} X X X$$

$$n_{i}x_{i} J_{H} S_{i}: i + \frac{K}{2} X$$

$$i (1)$$

The t are nearest neighbour hopping on a cubic lattice, $_{i}$ is the quenched binary disorder, with $_{i} = 0$ and value

, is the electron-phonon (EP) interaction, coupling electron density to the local distortion $x_{\rm i}$, K is the sti – ness, is the chem ical potential, and $J_{\rm H}$ is the H unds coupling. The parameters in the problem are =t, =t, electron density n, and temperature T. We treat the phonons and spins as classical (the adiabatic limit), assume $J_{\rm H}$ =t ! 1, and set β j = 1. We also set K = 1 and m easure energy, frequency, T, etc, in units of t.

The clean H-DE model was proposed early on [11] as a minimal model for the manganites, and a mean eld study [11] suggested strong decrease of T_c and increasing localisation with increase in EP coupling. M ore recently the H-DE model with 'cooperative phonons' has been analysed [12] in 3D, yielding a thermally driven MIT at low n but not near optimality. The e ect of disorder has been considered on EP-DE models but with focus mainly on phase coexistence [13] and bicriticality [3]. These studies yield insight on how disorder leads to cluster form ation near a rst order phase boundary [2,13], or its impact on a commensurate charge ordered phase [3], but do not have much bearing on the e ects observed, for example, at x = 0.3, where there is no obvious phase competetion. In our understanding, the e ects of disorder in the manganites, away from bicriticality, await an explanation. In this paper we overcom e a key technical lim itation of the earlier studies and provide new results on transport com bining the e ects of strong EP coupling, therm alspin uctuations, and quenched disorder, on lattices upto 12^3 in size.

Since we work with $J_H = t ! 1$, the electron spin is 'slaved' to the core spin orientation leading to an e ectively spinless, hopping disordered model: H = h_{iji} (t_{ij} $\stackrel{y}{i}$ $_{j}$ + h \mathfrak{c})+ $\stackrel{i}{\iota}$ ($_{i}$ $x_i)n_i + (K = 2) _i x_i^2$: The hopping am plitude depends on the spin orientations via $t_{ij}=t=\cos\frac{1}{2}\cos\frac{1}{2}+\sin\frac{1}{2}\sin\frac{1}{2}e^{i(i-j)}$, where i and i are respectively the polar and azim uthal angles of the spin S_i. We use our recently developed \travelling cluster approximation" (TCA) $\left[14\right]$ for solving the annealing problem on large lattices, by computing the energy cost of a MC update by constructing a cluster Ham iltonian', of N_c = L_c^3 sites, around the update site. W e w ill use N_c = 4^3 and, as docum ented earlier [14], this is su cient for equilibriating the spin and lattice variables. The electronic properties, e.g., resistivity, density of states, and optical response, are obtained by diagonalising the full electron H am iltonian on the equilibrium fx_i;S_ig con gurations, averaging therm ally and nally over 8 10 realisations of disorder f ig. The transport results are obtained using a form ulation described in detail previously [15]. We will use system size N = 8^3 , but have checked our results on N upto 12³. Our resistivity results are in units of $ha_0 = (e^2)$, where a_0 is the lattice spacing. As a rough estimate, = 1 in our units would correspond to 30 am .

Let us sum m arise the phases of the clean $H \rightarrow D \in m$ odel before addressing the e ects of disorder. (a): Structurally, a phase can be either charge ordered (CO), or charge disordered, i.e a polaron liquid (PL), or hom ogeneous, i.e a Fermi liquid (FL). (b): M agnetically it can be either ferrom agnetic (F) or param agnetic (P), and (c): in terms of electrical response it can be a h = tal', with d =dT > 0, or an insulator, with d =dT < 0.

C om bining these features, the ground state can be either a ferrom agnetic Ferm i liquid (F-FL), or F-PL, or F-CO, depending on and n, while nite T allow sP-FL, P-PL, and P-CO phases as well. Notice that while the threshold for single polaron trapping, i.e. n = 0, in 3D, is $E_p = {}^2=2K$ 5.4t, i.e. $_c(n = 0)$ 3.3 [16], at nite density the threshold for a collective PL is lower, e.g., $_c(n = 0.3)$ 2.6. These thresholds are further a ected

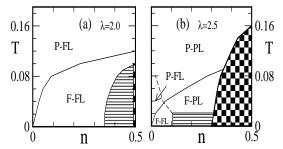


FIG.1. Phase diagram in the clean problem : (a) and (b) show the phase diagram at = 2.0 and = 2.5 respectively. The notation for the phases is explained in the text. The chessboard pattern is for a charge ordered (CO) phase with (;;) m odulation. Shaded regions represent coexistence.

by structural and spin disorder.

For < 2.0, Fig.1.(a), the phases are (i) F-FL at low T away from n = 0.5, (ii) P-FL at high T, and (iii) a F-CO phase at n = 0.5, separated from the F-FL, at low T, by a window of phase separation. For = 2.0 the T_c at n = 0.5 is suppressed with respect to the pure DE problem, but is still larger than the CO scale T_{CO}. At stronger coupling, of which = 2.5 is typical, Fig.1.(b); m uch of the phase diagram is taken up by insulating phases. As is increased beyond 2.5 the metallic window at low n shrinks quickly and all the phases turn insulating. The ground state, how ever, continues to be ferrom agnetic since we have not included any competing antiferrom agnetism (AF). From the resistivity we conmed that the clean model does not show a therm ally driven M IT except for n < 0:1, as noted earlier [12].

Even weak structural disorder dram atically a ects the electronic state at strong coupling, leading to metalinsulator transitions which are not present in the clean lim it. In the rest of the paper we focus on n = 0.3, typical of the high density metallic regime, and study the e ect of varying disorder and EP coupling. Since the r_A controlled bandwidth variation in real materials is relatively small we use only a 10% variation in =t about

= 2:0 and study the weak disorder regime, = 0 1:0. Disorder creates density inhom ogeneities in the FL which are amplied by the EP coupling, leading to a rapid rise in residual resistivity, and also opens up a window for the crucial F-FL to P-PL crossover. Fig 2.(a)

(c) show (T) with varying and illustrating the three broad transport regimes. At = 1.8, which is towards the lower end of our coupling range, moderate in– creases (0) but the overall (T) has the same nature as in the simple DE model [15] and neither EP coupling nor disorder seems to have any qualitative e ect. This < 0:6 and, we suggest, is akin to what</p> is true of one observes in La_{0:7}Sr_{0:3}M nO₃. At = 1:0, where $_{\rm M \ ott}$ we see hints of a weak downtum (0) > 100in (T) at high T. Overall, (T) at = 1:8 is mainly characterised by a F-FL to P-FL crossover. The density of states (DOS), Fig 2.(d), remains featureless at all T and the lattice distortions, Fig 2.(g), are weak with no signi cant variation across T_c . This \DE like" character in (T) survives up to = 22 in the clean lim it, see (c). However, for > 2:0 addition of weak Fig.2.(b)disorder (i) sharply increases (0) and creates a pseudogap in the DOS, (ii) maintains a regime with d = dT > 0for T < T_c, but (iii) crosses over to an `insulating' PL regime with d =dT < 0 for T $^{>}$ T_c. As Fig 2.(h) (i) indicate, these changes are associated with large lattice distortions and their variation across T_c. For 1:0 the ground state itself turns insulating for > 2.0. We provide a compact picture of the various M II in Fig.3, discussed later.

To gain insight on the F-FL to P-PL crossover we also calculated the 'e ective carrier number', $n_{eff}(!;T) =$

R!

(!;T)d!, at T = 0 and ! = 0:5, as well the density eld n (r;T). The com bination of n_{eff}, Fig.4.(a), the spatial patterns (not shown here) and the DOS, Fig.2.(e), suggest the following scenario at strong coupling and m oderate disorder: (i) there is polaronic localisation of a fraction of carriers (states at ! <) at T = 0, low ering neff, but the states at the chem ical potential rem ain extended, (ii) the polaronic states are further localised with increasing T due to DE spin disorder, while the delocalised electrons near experience scattering from the spin uctuations, leading to d = dT > 0, (iii) by the time Т T_c the net disorder arising from i, the lattice distortions, and spin disorder is so large that the system is e ectively at a localisation transition on the complex f i;xi;Sig background: the states at also get localised, (iv) the T > T_c phase has a modest h obility gap' (at moderate;) so there is no simple activated behaviour. The pseudogap in the DOS, Fig 2.(e), deepens initially and gradually lls up for $T > T_c$.

Let us consider the relevance of these results to m anganites at x 0:3 0:4, away from commensurate lling and charge ordering instabilities. The mean hopping amplitude between M n ions, via the oxygen orbitals, is controlled by r_A through the M n-O-M n bond angle. The mism atch between di erent A site cations is quanti ed through the variance, $_A$, of the ionic size, and acts as

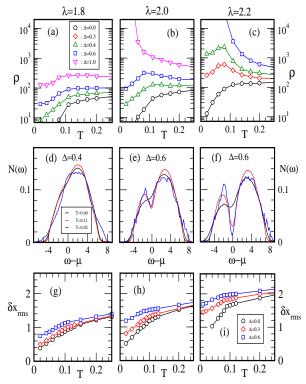


FIG.2. Colour online: Resistivity, (T), DOS, and lattice distortion at n = 0.3. (a) (c): (T), with varying and . (d) (f):DOS, N (!;T) for the indicated parameters. (g) (i):RMS lattice distortion, $x_{rm \ s} = \frac{P}{h(x_i \ x \ r)}$, where x is the system averaged distortion.

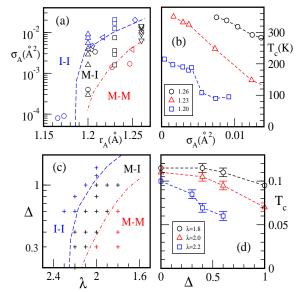


FIG.3. Colour online: Transport regimes and ferrom agnetic $T_{\rm c}$: comparing data on the x = 0.3 m anganites with our n = 0.3 results. (a):Transport phase diagram ' indicating the nature of low T to high T crossover with changing $r_{\rm A}$ and $_{\rm A}$, data from Ref[6–9] (b):T_c($_{\rm A}$;r_A) in the m anganites, from Ref[6–7], (c) transport crossovers from our calculation, and (d):our results on T_c(;).

disorder on the electronic system . For a material of composition $A_1 \times A_x^0 M$ nO₃, say, r_A and A depends on the radius of the A, A' ions as well as x. To disentangle the e ect of varying carrier density (x) from that of varying boupling constants', there have been system atic studies of the manganites at xed x, with controlled variation in r_A , related to our =t ratio, and A, related to our =t.

Focusing initially on x = 0.3, the data from a wide variety of sources can be organised in term s of the transport response, (T), and magnetic T_c . We choose a simple characterisation where we construct the M IT phase diagram in terms of the low T to high T crossover observed in (T). For example, La_{0:7}Sr_{0:3}M nO₃ (LaSr), is a metal at both low T and T > $\rm T_{c}$ so it shows M -M crossover. In that spirit LaC a shows M -I crossover, while PrC a is I-I. These simple binary' cationic systems are well studied, have relatively sm all $_{\rm A}$, and the transport response can be argued to arise m ainly from variations in r_A . However, m ore com plex cationic com binations have been used, notably by Att eld and cow orkers [6,7], to vary _A at xed r_A and x. Our organisation of the experimental data, Fig.3.(a) uses three such fam ilies, at $r_A = 1.26$; 1.23 and 1:20A, aswellas data from other sources [8,9] to highlight the combined impact of r_A and $_A$ variation on transport character. W e have used the 9 fold coordinated values of ionic radius from Shannon [17] in computing r_A and $_A$ for about 30 com positions.

Four features are notable in the experim ental MIT and T_c data, Fig.3.(a) (b), at x = 0.3: (i) the clean' lim it allows only a narrow window, r_A 1:18 1:20A, for M-I

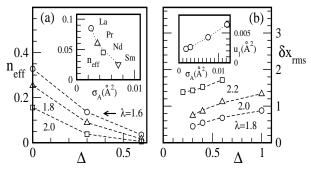


FIG.4. (a) C om puted optical spectral weight, n_{eff} , at cuto ! = 0.5t and T = 0.01 for varying and . Inset: data from Ref[10] on LaSr, etc, at x = 0.4, ! = 0.1eV, plotted versus _A. The r_A values, LaSr downwards, are 1.256 A, 1.232 A, 1.22 A and 1.202 A. (b) O ur results on disorder induced lattice distortion at T = 0.01. Inset shows the _A induced increase in the mean square oxygen displacement at low T in a sequence of x = 0.3 and $r_A = 1.23$ A m anganites, from Ref[6].

crossover, (ii) the M-I region broadens with increasing A at the cost of the M-M region (red/dot-dash line), disorder can induœ a therm ally driven M II, (iii) at T = 0 just increasing A can drive a metallic ground state insulating (blue/dashed line), (iv) the same A has much stronger impact on transport and T_c at small r_A compared to 0:01A² has only modest eflarge r_A , for example $_A$ fect on T_c at $r_A = 126A$, but leads to a large reduction at r_A < 1:23A.W hile we cannot make a direct num erical correspondence between A and =t, etc, our results on transport crossovers, Fig.3.(c), and T_c , Fig.3.(d), show (iv) above are correctly reprothat all the trends (i) duced. A t to the detailed T dependence of resistivity will of course require a more sophisticated phonon model. Our T_c^{m ax} 0:12t 300K (fort 0:25eV) com pares reasonably with the maximum in Fig.3.(b).

A lthough the sim ilarity of our results to experim ental data on the manganites seems persuasive, let us exam ine how these results may be modi ed in a more realistic model. (i) The manganites involve two e_{α} orbitals coupled to Jahn-Teller (JT) phonons, with the possibility of orbital order. Our prelim inary calculations with the 2 band JT model in 2D [18] suggests that for x 0:3 0:4 there is no non trivial orbital order and the transport response is sim ilar to what we observe here. The one band m odel does not capture the correct physics as x ! 0, or x = 0.5, but appears reasonable for x 0:3 0:4. (ii) The oxygen atom s are corner shared among M nO $_6$ octahedra so the phonon variables are cooperative. W e have not explored this aspect but believe the main e ects would be lower critical EP coupling for localisation [12] and possibly a sharper M IT $across T_c$. (iii) There are AF interactions present in the m anganites. W e repeated the d-H-DE calculation in the presence of AF coupling and discovered that it leads to a sharper drop in T_c, shifts the M II phase boundaries som ew hat, and leads to an AF-I or . The qualitative results of this phase at large

paper, however, remain una ected.

Finally, if our argument about disorder induced polaron formation is correct then the following features should be experimentally observed with increasing $_{\rm A}$: (a) systematic suppression of low frequency optical spectral weight, $n_{\rm eff}$ at ! $^<$ 0:1eV, at low T, (b) increase in the incoherent lattice distortion (oxygen Debye-W aller factor), progressively larger at smaller $r_{\rm A}$, and (c) appearance of an increasingly deeper pseudogap in the tunneling DOS at low T. Fig.2 and Fig.4 quantify these e ects. Experiments in the recent past do claim disorder induced polaron formation in La_{0:54}Ba_{0:46}M nO₃ [19] but more direct con mation for x 0:3 is desirable.

To conclude, we have studied a model with Holstein phonons, double exchange and quenched disorder, and illustrated the disorder enhancement of polaronic tendency and its interplay with spin uctuations. Our results compare well with the disorder dependence of transport and T_c observed in the bptim ally doped' manganites. We make three testable predictions regarding the behaviour of optical spectral weight, oxygen D ebye-W aller factor and tunneling density of states for controlled variations of $_A$ in these materials.

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